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List of Publications

1. *"Anomalous Hall effect in Cu doped Bi2Te3 topological insulator"* ***Mahima Singh***, *Abhishek Singh, et al. J. Phys.: Condens. Matter* ***32,*** *305602 (2020).*
2. *"Evidence of surface and bulk magnetic ordering in Fe and Mn doped Bi2Se3 topological insulator"* ***Mahima Singh,*** *et al. Appl. Phys. Lett.* ***118****, 132409 (2021).*
3. *"Correlation between switching over Weak Antilocalization (WAL) to Weak Localization (WL) and coexistance of positive and negative magnetoresistance in S doped Bi1.5Sb0.5Te1.3Se1.7-ySy"* ***Mahima Singh,*** *et al. (Under review).*
4. *"Study of Transport properties of BiFeSeS"* ***Mahima Singh,*** *et al. (communicated).*
5. *"Presence of Anomalous Hall Effect in Nonmagnetic Bi1.90Mo0.10Se3"* ***Mahima Singh,*** *et al. (To be communicated).*
6. *"Pressure induced superconducting state in ideal topological insulator $BiSbTe_3$" Vinod K. Gangwar, Shiv Kumar,* ***Mahima singh*** *et al. Phys. Scr.* ***96****, 055802 (2021).*
7. *"Observation of antiferromagnetic ordering from μ-SR study and Kondo effect in Dy doped Bi_2Se_3 topological insulator" Vinod K. Gangwar, Shiv Kumar,* ***Mahima singh*** *et al. J. Phys. D: Appl. Phys. 54 455302 (2021).*
8. *"Defect induced ferromagnetic ordering and room temperaturenegative magnetoresistance in MoTeP" Debarati Pal, Shiv Kumar, Prashant Shahi, Sambhab Dan, Abhineet Verma , Vinod K. Gangwar,* ***Mahima Singh*** *et al. Sci. reports 11:9104 (2021).*
9. *"Pressure induced topological and structural transitions in iron and sulphur doped Sb2Te3" D. Pal, B. Sharma, Shambhav Dan, Vinod K. Gangwar,* ***Mahima singh*** *et al. Materials Letters 320, 130401 (2021).*

Schools / Meetings / Workshops / Conference Attended

1. International Conference on "Advances in Bilological System and Materials Science in NanoWorld" (ABSMSNW-2017), Department of Physics, IIT (BHU), Vranasi, 19-23 February 2017.

2. National Conference on "Optics Photonics and Syncrotron Radiation For Technological Applications" (OPSR-2018), Raja Ramanna Center for Advanced Technology, Indore 29th April to 2nd May 2018.

3. First Indian Materials Conclave (IndMac) & 30th Annual General Meeting of MRSI, IISC Bangalore, 12-15th February 2019.

4. "64th DAE Solid State Physics Symposium" organized by BARC Mumbai, IIT Jodhpur Rajasthan, 18-22th December 2019.

5. "International Conference on Functional Nanomaterials (ICFNM-2019)", IIT BHU, Varanasi, 22-25th February 2019.

6. "Advances in Materials Science and Technology (WSAMST-2020)" held during 23-26 june 2020 by the Department of Applied Sciences and Humanities (Physics), School of Engineering, University of Petroleum and Energy Studies, Dehradun.

7. "Advanced Physical Tools and Techniques for Materials Characterization" APTTMC-2020, Mahatma Gandhi Central University, Motihari-Bihar.

8. "Synthesis and Characterization of Smart Materials and Their Potential Applications" (ISSCSMPA-2020), University School of basic and Applied Sciences Guru Gobind Singh Indraprastha University, New Delhi-110078, India.